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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>DS</u>	AA	6,303,094	M. Kusunoki, et al.	10/16/01	—	—
<u>DS</u>	AB	6,278,231	T. Iwasaki, et al.	08/21/01	—	—
—	AC					
—	AD					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)	
<u>DS</u>	AE	10-265208	10/06/98	Japan	Yes-Abstract/Corresponds to USP 6303094/Discussed in the specification
<u>DS</u>	AF	2000-31462	01/28/00	Japan	Yes-Abstract/Corresponds to USP 6278231/Discussed in the specification
	AG				

OTHER DOCUMENTS

<u>DS</u>	AH	P.P. Ruden, et al.; "Extrinsic Performance Limitations of AlGaIn/GaN Heterostructure Field Effect Transistors"; <i>MRS Internet J. Nitride Semicond. Res.</i> ; 4S1, G6.35; 1999 (6 pages.)/Discussed in the specification	
<u>DS</u>	AI	P. Kim, et al.; "Thermal Transport Measurements of Individual Multiwalled Nanotubes"; <i>Physical Review Letters</i> 87; 215502; November 19, 2001./Discussed in the specification	
<u>DS</u>	AJ	M. Kusunoki, et al.; "A formation mechanism of carbon nanotube films on SiC(0001); <i>Applied Physics Letters</i> ; Vol. 77; Issue 4; July 24, 2000; p. 531./Discussed in the specification	
Examiner	<u>DS</u>	Date Considered	5/30/06